

COMPLEMENTARY SILICON POWER TRANSISTORS

- SGS-THOMSON PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES
- FULLY MOLDED ISOLATED PACKAGE
- 2000 V DC ISOLATION (U.L. COMPLIANT)

APPLICATIONS

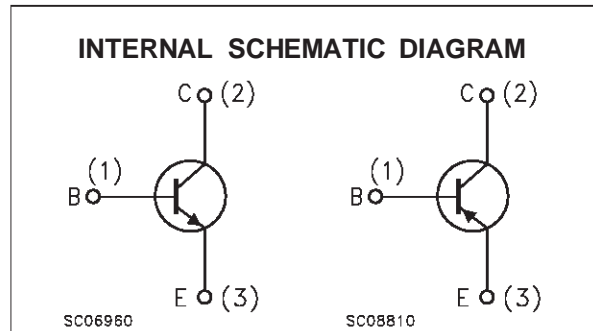
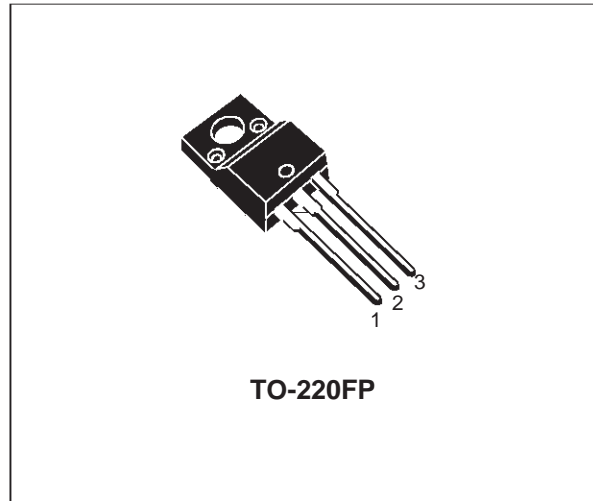
- GENERAL PURPOSE SWITCHING
- GENERAL PURPOSE AMPLIFIERS

DESCRIPTION

The BD241BFP is silicon epitaxial-base NPN transistors mounted in TO-220FP fully molded isolated package.

It is intended for power linear and switching applications.

The complementary PNP types is the BD242BFP.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		NPN	BD241BFP	
		PNP	BD242BFP	
V_{CER}	Collector-Base Voltage ($R_{BE} = 100 \Omega$)		90	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)		80	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)		5	V
I_C	Collector Current		3	A
I_{CM}	Collector Peak Current		5	A
I_B	Base Current		1	A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$		24	W
T_{stg}	Storage Temperature		-65 to 150	$^\circ C$
T_j	Max. Operating Junction Temperature		150	$^\circ C$

For PNP types voltage and current values are negative.

BD241BFP / BD242BFP

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	5.3	°C/W
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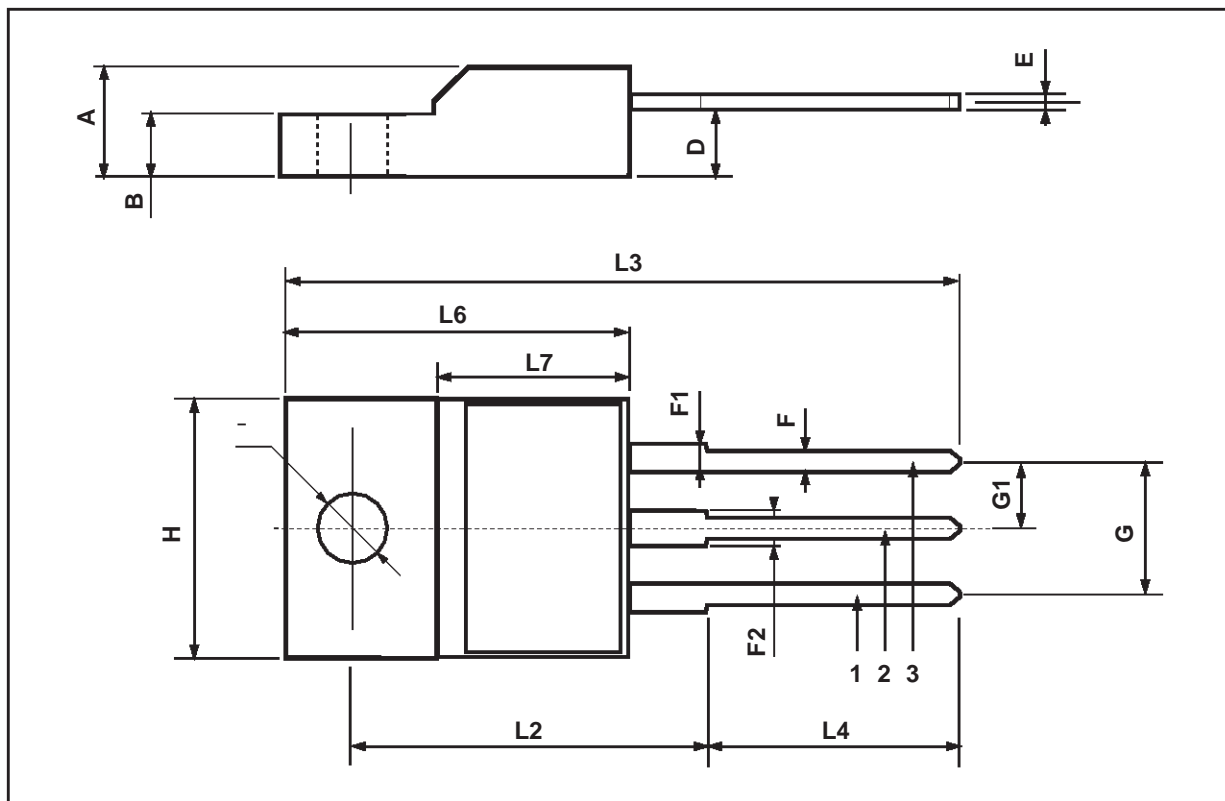
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 60 V			0.3	mA
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 80 V			0.2	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA	80			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 3 A I _B = 0.6 A			1.2	V
V _{BE(ON)*}	Base-Emitter Voltage	I _C = 3 A V _{CE} = 4 V			1.8	V
h _{FE*}	DC Current Gain	I _C = 1 A V _{CE} = 4 V I _C = 3 A V _{CE} = 4 V	25 10			

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %
For PNP types voltage and current values are negative.

TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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